

2MBI200VH-170-50

IGBT Modules

IGBT MODULE (V series) 1700V / 200A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines

Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)



Items	Symbols	Conditions	Conditions		Units		
Collector-Emitter voltage	Vces				V		
Gate-Emitter voltage	V _{GES}				V		
Collector current	Ic	Continuous	Tc=25°C	200			
		Continuous	Tc=100°C	310			
	I _{C pulse}	1ms		400	Α		
	-Ic			200			
	-I _{C pulse}	1ms	1ms				
Collector power dissipation	Pc	1 device	1 device		W		
Junction temperature	T _j			175	°C		
Operating junction temperature (under switching conditions)	Tjop			150			
Case temperature	Tc			125			
Storage temperature	T _{stg}						
Isolation voltage between terminal and copper base (*1)	Viso	AC: 1min.	AC : 1min.		4000		VAC
Screw torque Mounting (*2)	-			6.0	N m		
Terminals (*3)	-			5.0	IN III		

Note *1: All terminals should be connected together during the test. Note *2: Recommendable Value : $3.0\text{-}6.0~\text{N}\cdot\text{m}$ (M5 or M6) Note *3: Recommendable Value : $2.5\text{-}5.0~\text{N}\cdot\text{m}$ (M5)

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

lta	Symbols	Conditions		Characteristics			Heite
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1700V		-	-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 200mA		6.0	6.5	7.0	V
Collector-Emitter saturation voltage	V	V _{GE} = 15V	T _j =25°C	-	2.15	2.60	V
	VCE (sat)		T _j =125°C	-	2.55	-	
	(terminal)		T _j =150°C	-	2.60	-	
	V	Ic = 200A	T _j =25°C	-	2.00	2.25	
	V _{CE} (sat)		T _j =125°C	-	2.40	-	
	(chip)		T _j =150°C	-	2.45	-	
Internal gate resistance	R _G (int)	-		-	3.8	-	Ω
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	19	-	nF
Turn-on time	ton	V_{cc} = 900V, I_{c} = 200A V_{GE} = ±15V, Rg_on= 6.8Ω, Rg_off= 3.6Ω T_{j} =150°C, L_{s} = 30nH		-	1150	-	nsec
	tr			-	580	-	
	t _{r (i)}			-	60	-	
Turn-off time	toff			-	1050	-	
	t f			-	140	-	
Forward on voltage	\/	V _{GE} = 0V I _F = 200A	T _j =25°C	-	1.95	2.40	V
	V _F		T _j =125°C	-	2.20	-	
	(terminal)		T _j =150°C	-	2.20	-	
	V		T _j =25°C	-	1.80	2.25	
	V _F		T _j =125°C	-	2.05	-	
	(chip)		T _j =150°C	-	2.05	-	
Reverse recovery time	trr	I _E = 200A		-	220	-	nsec

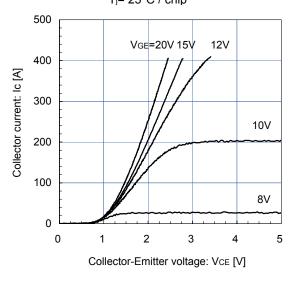
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
		Conditions	min.	typ.	max.	Ullits
Thermal resistance(1device)	R _{th(j-c)}	IGBT	-	-	0.120	°C/W
		FWD	-	-	0.160	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.0125	-	

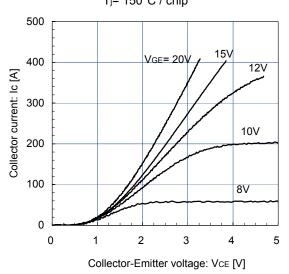
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.) T_{j} = 25°C / chip

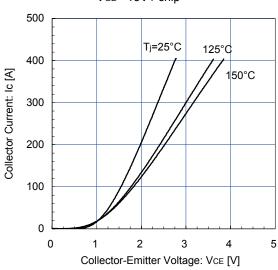


Collector current vs. Collector-Emitter voltage (typ.) T_j= 150°C / chip

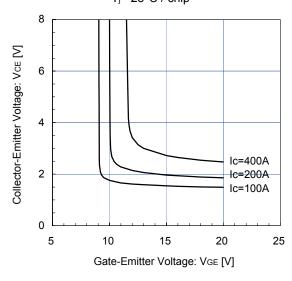


Collector current vs. Collector-Emitter voltage (typ.)

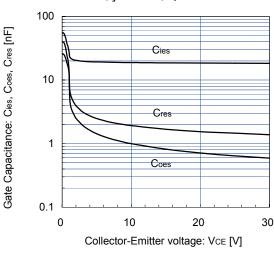
VGE= 15V / chip



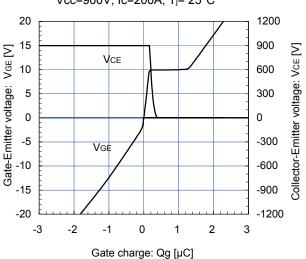
Collector-Emitter voltage vs. Gate-Emitter voltage Tj= 25°C / chip



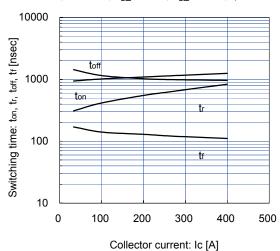
Gate Capacitance vs. Collector-Emitter Voltage VGE= 0V, f= 1MHz, Tj= 25°C



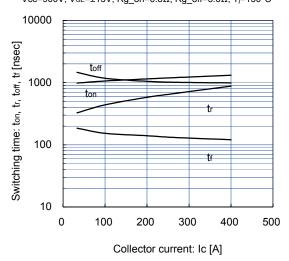
Dynamic Gate Charge (typ.) Vcc=900V, Ic=200A, T_i= 25°C



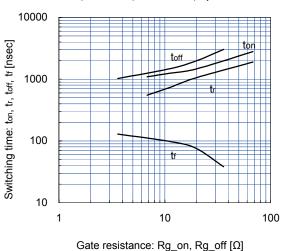
Switching time vs. Collector current (typ.) Vcc=900V, $VgE=\pm15V$, $Rg_on=6.8\Omega$, $Rg_off=3.6\Omega$, $T_j=125^{\circ}C$



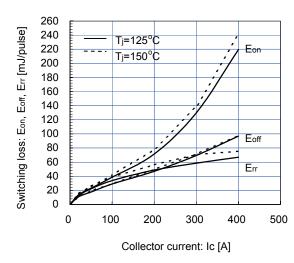
Switching time vs. Collector current (typ.) Vcc=900V, VcE=±15V, Rg_on=6.8 Ω , Rg_off=3.6 Ω , Tj=150°C



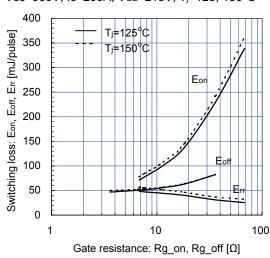
Switching time vs. Gate resistance (typ.) Vcc=900V, Ic=200A, VGE=±15V, Ti=125°C



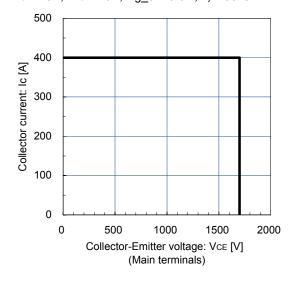
Switching loss vs. Collector current (typ.) Vcc=900V, VgE= \pm 15V, Rg_on= 6.8Ω , Rg_off= 3.6Ω



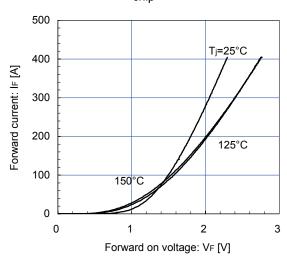
Switching loss vs. Gate resistance (typ.) Vcc=900V, Ic=200A, VgE=±15V, Tj=125, 150°C



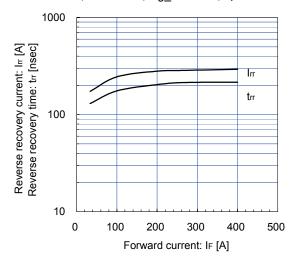
Reverse bias safe operating area (max.) +V_{GE}=15V, -V_{GE}=15V, Rg_off=3.6 Ω , Tj=150°C



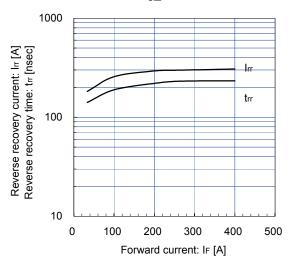
Forward Current vs. Forward Voltage (typ.) chip



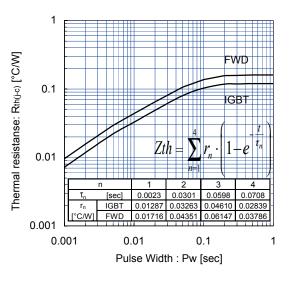
Reverse Recovery Characteristics (typ.) Vcc=900V, $VgE=\pm15V$, $Rg_on=6.8\Omega$, $T_j=125^{\circ}C$



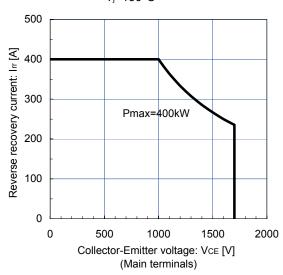
Reverse Recovery Characteristics (typ.) Vcc=900V, $VgE=\pm15V$, $Rg_on=6.8\Omega$, $Tj=150^{\circ}C$



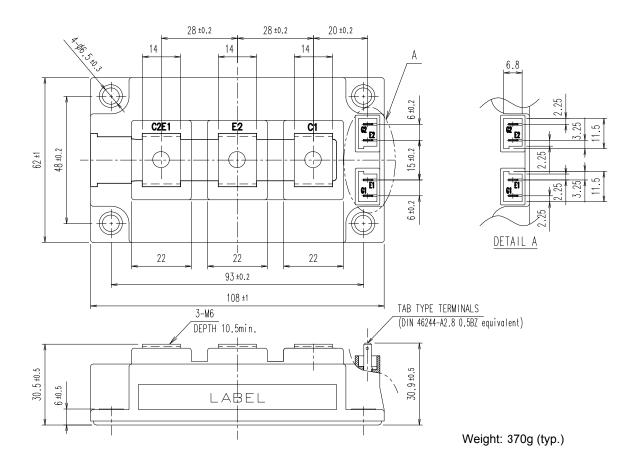
Transient Thermal Resistance (max.)



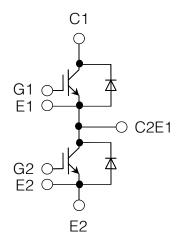
FWD safe operating area (max.) $T_i=150$ °C



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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- Measurement equipment

- Machine tools
- Audiovisual equipment
- Electrical home appliances
 Personal equipment (terminal devices)
- Personal equipment
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• Traffic-signal control equipment

- Gas leakage detectors with an auto-shut-off feature
- Emergency equipment for responding to disasters and anti-burglary devices
 Medical equipment
- Safety devices

- modical equipment
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